Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT54 (TO-92) plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct gate triggering from low power drivers and logic ICs
- · High commutation capability with very sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

3. Applications

- Low power motor controls
- · Small inductive loads e.g. solenoids, door locks, water valves
- Small loads in large white goods

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	1000	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	9	A
T _j	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 70 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	0.8	A
Static charact	eristics			•		
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	0.25	-	5	mA





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	0.25	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	0.25	-	5	mA
Dynamic cha	racteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 670 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	150	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 1 V/µs; gate open circuit	1	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2—T1
2	G	gate		G sym051
3	T1	main terminal 1	321	7
			TO-92 (SOT54)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA2008-1000D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BTA2008-1000D/L01	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Marking

Table 4. Marking codes

Type number	Marking code
BTA2008-1000D	200810D
BTA2008-1000D/L01	

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	1000	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 70 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	0.8	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	9	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	9.9	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	0.41	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 1.5 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	1	Α
P_GM	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

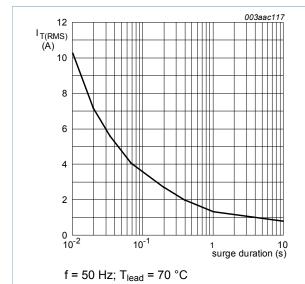


Fig. 1. RMS on-state current as a function of surge duration; maximum values

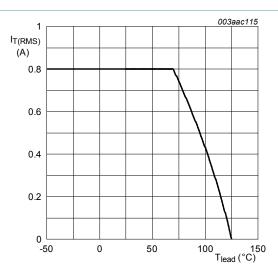


Fig. 2. RMS on-state current as a function of lead temperature; maximum values

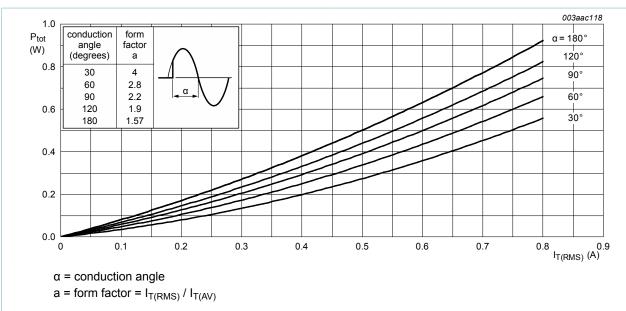


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

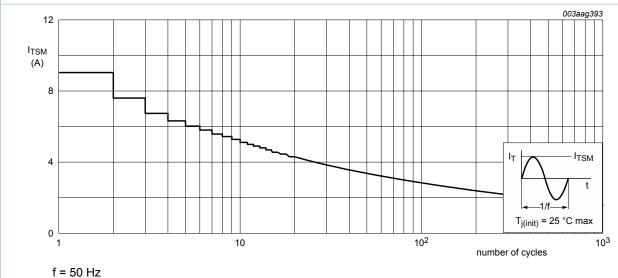
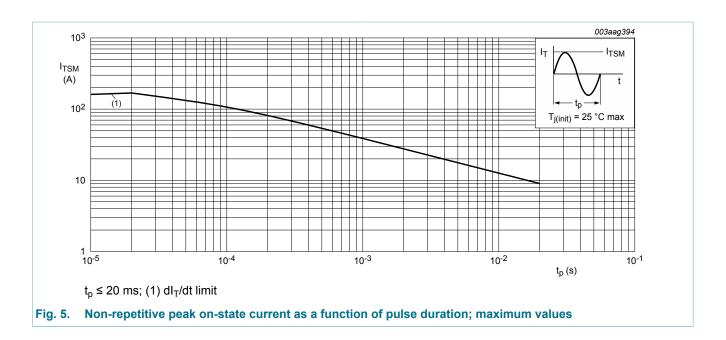


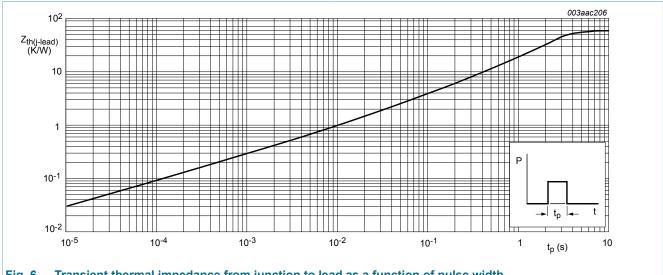
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



Thermal characteristics

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

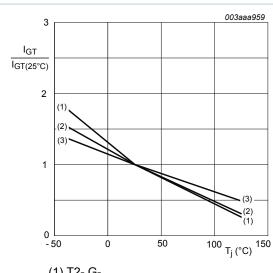


Transient thermal impedance from junction to lead as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	0.25	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
IL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	10	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.85	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.2	0.3	-	V
I _D	off-state current	V _D = 1000 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics		'			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 670 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	150	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 10 V/ μ s; gate open circuit	0.5	-	-	A/ms
		V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 1 V/µs; gate open circuit	1	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

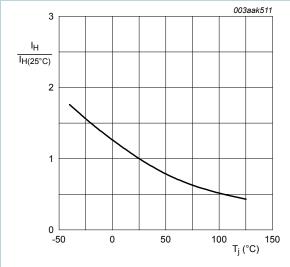


Fig. 9. Normalized holding current as a function of junction temperature

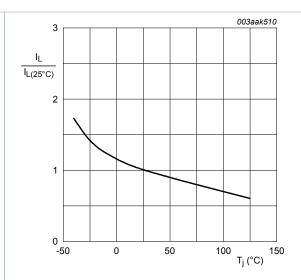
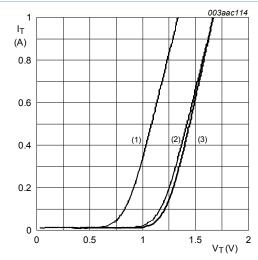
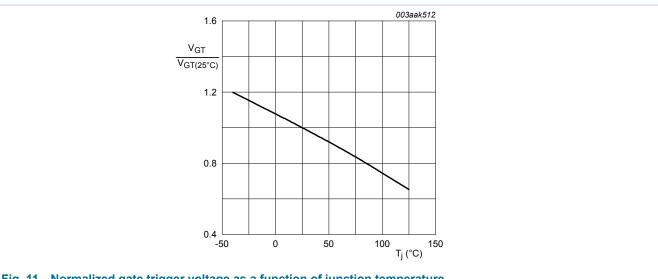


Fig. 8. Normalized latching current as a function of junction temperature



- $V_{o} = 0.835 \text{ V}; R_{s} = 0.50 \Omega$
- (1) T_j = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage



11. Package outline

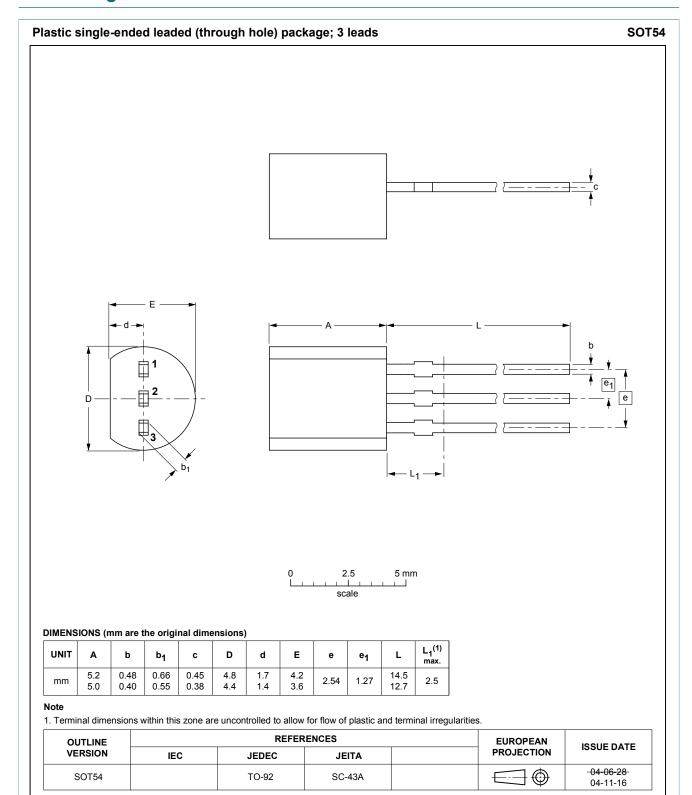


Fig. 12. Package outline TO-92 (SOT54)

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